DISCRETE SEMICONDUCTORS



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### Schottky barrier double diodes

### FEATURES

• Low switching losses

**Philips Semiconductors** 

- High breakdown voltage
- Fast recovery time
- Guard ring protected
- Plastic SMD package.

### APPLICATIONS

- Low power, switched-mode power supplies
- Rectifying
- Polarity protection.

### DESCRIPTION

The PBYR2100CT series consists of Schottky barrier double diodes, fabricated in planar technology, and encapsulated in SOT223 plastic SMD packages.

### PINNING

PIN	IN DESCRIPTION	
1	anode (a <sub>1</sub> )	
2	common cathode	
3	anode (a <sub>2</sub> )	
4	common cathode	

# MARKING

TYPE NUMBER	MARKING CODE
PBYR280CT	BYR28
PBYR290CT	BYR29
PBYR2100CT	BYR210



## **PBYR2100CT series**

# PBYR2100CT series

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode		1		-	-
V <sub>R</sub>	continuous reverse voltage				
	PBYR280CT		_	80	V
	PBYR290CT		_	90	V
	PBYR2100CT		_	100	V
V <sub>RRM</sub>	repetitive peak reverse voltage				
	PBYR280CT		_	80	V
	PBYR290CT		_	90	V
	PBYR2100CT		-	100	V
V <sub>RWM</sub>	crest working reverse voltage				
	PBYR280CT		_	80	V
	PBYR290CT		-	90	V
	PBYR2100CT		_	100	V
I <sub>F(AV)</sub>	average forward current	$T_{amb} = 85 \text{ °C}; \text{ see Fig.2}; \\ R_{th j-a} = 70 \text{ K/W}; \text{ note 1}; \\ V_{R(equiv)} = 0.2 \text{ V}; \text{ note 2}$	-	1	A
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8.3 μs half sine wave; JEDEC method	-	10	A
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	-	0.5	A
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C
T <sub>amb</sub>	operating ambient temperature		_	85	°C

#### Notes

- 1. Refer to SOT223 standard mounting conditions.
- 2. For Schottky barrier diodes thermal run-away has to be considered, as in some applications, the reverse power losses  $P_R$  are a significant part of the total power losses. Nomograms for determination of the reverse power losses  $P_R$  and  $I_{F(AV)}$  rating will be available on request.

## PBYR2100CT series

### **ELECTRICAL CHARACTERISTICS**

 $T_{amb} = 25 \ ^{\circ}C$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode						
V <sub>F</sub>	forward voltage	see Fig.3				
		I <sub>F</sub> = 1 A; note 1	-	-	790	mV
		I <sub>F</sub> = 1 A; T <sub>j</sub> = 100 °C; note 1	-	-	690	mV
I <sub>R</sub>	reverse current	$V_R = V_{RRMmax}$ ; note 1; see Fig.4	-	-	0.5	mA
		V <sub>R</sub> = V <sub>RRMmax</sub> ; T <sub>j</sub> = 100 °C; note 1; see Fig.4	-	-	5	mA
C <sub>d</sub>	diode capacitance	$V_R = 4 V$ ; f = 1 MHz; see Fig.5	_	_	100	pF

#### Note

1. Pulsed test:  $t_p = 300 \ \mu s$ ;  $\delta = 0.02$ .

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	70	K/W

#### Note

1. Refer to SOT223 standard mounting conditions.

<sup>1.2</sup> V<sub>F</sub> (V) <sup>1.6</sup>

MSA896

100

V<sub>R</sub> (V)

0.8

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#### **GRAPHICAL DATA**



(1) T<sub>amb</sub> = 25 °C. (2) T<sub>amb</sub> = 85 °C. (3) T<sub>amb</sub> = 100 °C. (4) T<sub>amb</sub> = 125 °C.

(5)  $T_{amb} = 150 \ ^{\circ}C.$ 

Reverse current as a function of reverse



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Fig.5 Diode capacitance as a function of reverse voltage; typical values.

# PBYR2100CT series

### PACKAGE OUTLINE



### PBYR2100CT series

### DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.			
Product specification	This data sheet contains final product specifications.			
Limiting values				
more of the limiting values of the device at these or at	accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or may cause permanent damage to the device. These are stress ratings only and operation any other conditions above those given in the Characteristics sections of the specification limiting values for extended periods may affect device reliability.			
Application information				
Where application informat	on is given, it is advisory and does not form part of the specification.			

#### LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.